Electronic supplementary information for

Two-dimensional $InTeClO_3$: an ultrawide-bandgap material with potential application in deep ultraviolet photodetector

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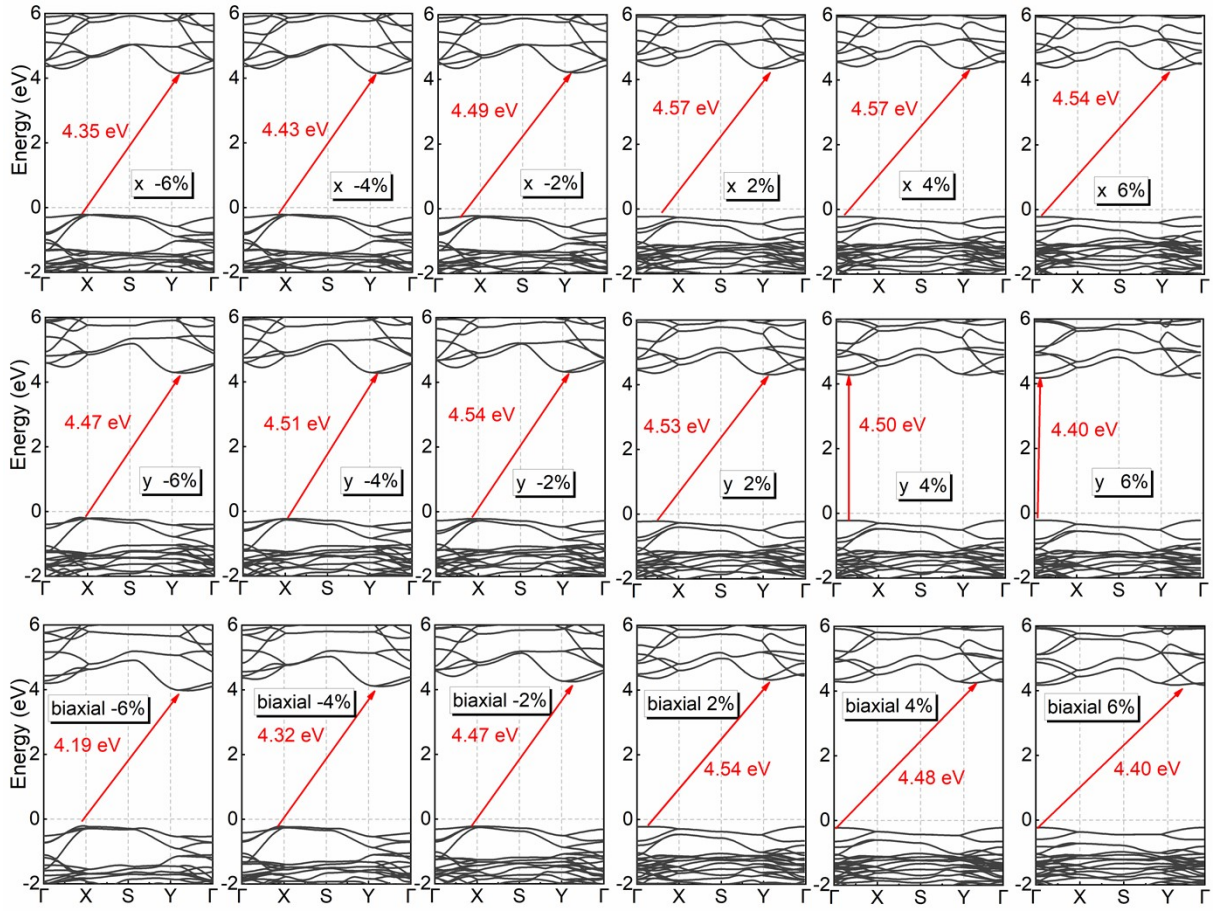

Fig. S1. The band structures of the $InTeClO_3$ monolayer under in-plane strain from −6% to 6% along the uniaxial and biaxial directions, respectively. The bandgap is highlighted in red. Fermi level is set to zero.

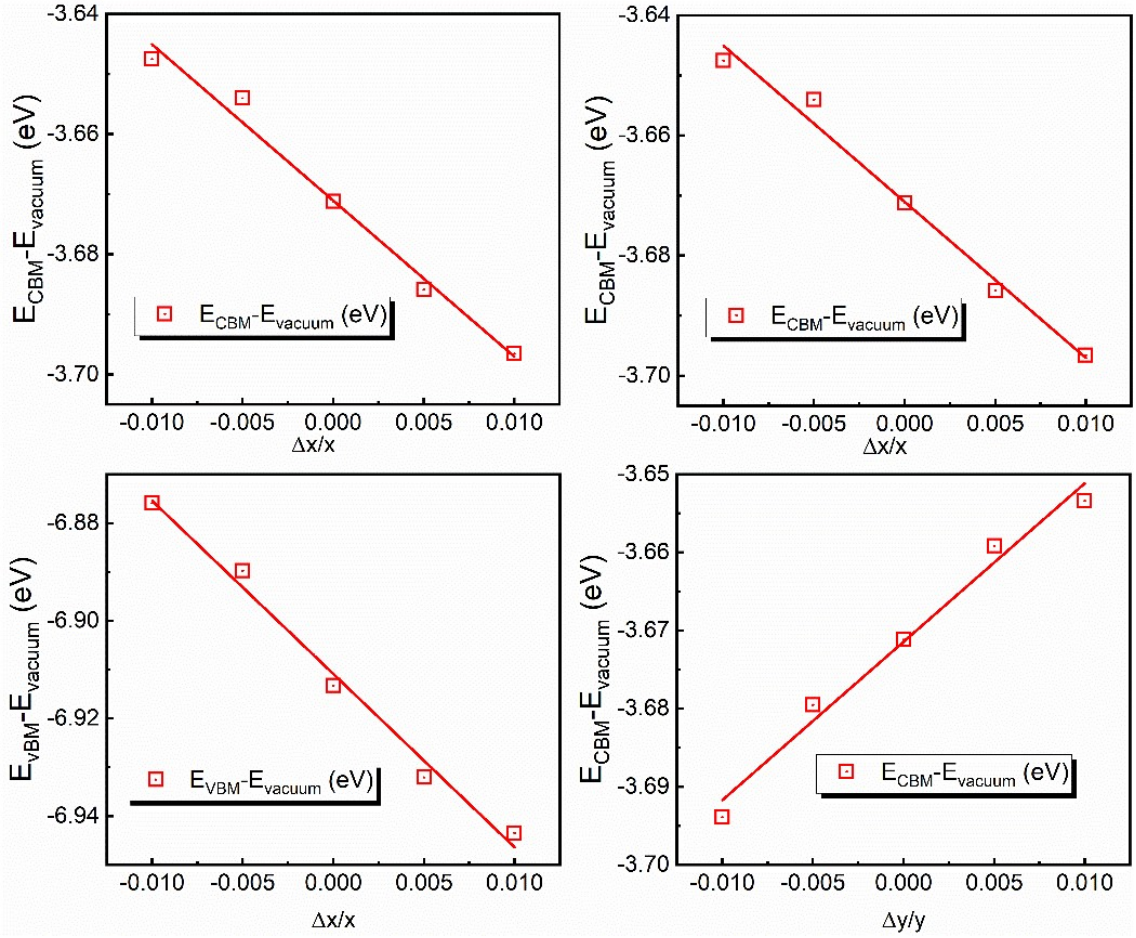

Fig. S2. Evaluations of band edges of monolayer $InTeClO_3$ relative to vacuum with respect to strains along the *x* and *y* directions, respectively. The slope is the deformation potential E_d.